

1 (i) CLAIMS

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3 What is claimed is:

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7 A microwave filter comprising:

8
9 a first piezoelectric acoustic, bulk wave, resonator
10 having a piezoelectric layer made of an insulating material;

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12 a second piezoelectric acoustic, bulk wave, resonator
13 having a piezoelectric layer made of an insulating material, the
14 second acoustic resonator being acoustically coupled to the first
15 acoustic resonator; and

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17 a plurality of intervening layers of material located
18 between the first acoustic resonator and the second acoustic
19 resonator and affecting the amount of the acoustic coupling
20 between the first and second acoustic resonators.

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24 The microwave filter of claim 1 wherein the first
25 acoustic resonator and the second acoustic resonator are
26 acoustically either approximately critically coupled or over-
27 coupled.

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a first piezoelectric acoustic, bulk wave, resonator;

a plurality of intervening layers of material located between the first acoustic resonator and the second acoustic resonator and affecting the amount of the acoustic coupling between the first and second acoustic resonators and the first acoustic resonator and the second acoustic resonator being acoustically either approximately critically coupled or over-coupled.

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3 The microwave filter of claim 4 having a signal input port
4 and a signal output port, the first acoustic resonator being
5 electrically connected to the signal input port and the second
6 acoustic resonator being electrically connected to the signal
7 output port.

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11 A microwave filter comprising:

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13 a first piezoelectric acoustic, bulk wave, resonator;

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15 a second piezoelectric acoustic, bulk wave, resonator
16 acoustically coupled to the first acoustic resonator;

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18 a third piezoelectric acoustic, bulk wave, resonator
19 electrically connected to the second acoustic resonator;

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21 a fourth piezoelectric acoustic, bulk wave, resonator
22 acoustically coupled to the third acoustic resonator;

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24 a first plurality of intervening layers of material
25 located between the first acoustic resonator and the second
26 acoustic resonator and affecting the amount of the acoustic
27 coupling between the first and second acoustic resonators; and
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1 a second plurality of intervening layers of material
2 located between the third acoustic resonator and the fourth
3 acoustic resonator and affecting the amount of the acoustic
4 coupling between the third and fourth acoustic resonators.

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8 The microwave device of claim 6 in which the first,
9 second, third and fourth acoustic resonators each has a
10 piezoelectric layer made of an insulating material.

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14 The microwave device of claim 6 having a signal input port
15 and a signal output port, the first acoustic resonator being
16 connected to the signal input port and the fourth acoustic
17 resonator being connected to the signal output port.

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21 The microwave device of claim 6 in which at least two of
22 the acoustic resonators include piezoelectric layers of material
23 and electrodes, each of said resonators having a resonant
24 frequency, at least one electrode of the first one of said at
25 least two acoustic resonators having a thickness that differs from
26 the thickness of at least one of the electrodes in the second
27 resonator of said at least two acoustic resonators thereby
28 offsetting the resonant frequency of the first one of said at

1 least two acoustic resonators from the resonant frequency of the
2 second one of said at least two acoustic resonators.

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6 A microwave filter having a signal input port and a
7 signal output port and comprising:

9 a first acoustic, bulk wave, resonator that includes a
10 piezoelectric layer of material, the first acoustic resonator
11 being electrically connected to the signal input port;

13 a second acoustic, bulk wave, resonator acoustically
14 coupled to the first resonator;

16 a third acoustic, bulk wave, resonator that includes a
17 piezoelectric layer of material and that is acoustically coupled
18 to the second resonator, the third acoustic resonator being
19 electrically connected to the signal output port and the second
20 acoustic resonator being located between the first and third
21 acoustic resonators;

23 a first plurality of intervening layers of material
24 located between the first acoustic resonator and the second
25 acoustic resonator and affecting the acoustic coupling between
26 the first and second acoustic resonators;

1 a second plurality of intervening layers of material
2 located between the second and third acoustic resonators and
3 affecting the acoustic coupling between the second and third
4 acoustic resonators.

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8 The microwave filter of claim 10 in which the second
9 acoustic resonator includes a piezoelectric layer of material and
10 bounding electrodes and in which the second acoustic resonator is
11 electrically connected to an external load.

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15 The microwave filter of claim 1 and further comprising:

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17 a substrate;

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19 an acoustic reflector; and

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21 the first and second acoustic resonators and the plurality
22 of intervening layers being supported upon the substrate by the
23 acoustic reflector.

The microwave filter of claim 4 and further comprising:

a substrate;

an acoustic reflector; and

the first and second acoustic resonators and the plurality of intervening layers being supported upon the substrate by the acoustic reflector.

The microwave filter of claim 6 and further comprising:

a substrate;

an acoustic reflector; and

the first, second, third and fourth acoustic resonators and the first and second plurality of intervening layers being supported upon the substrate by the acoustic reflector.

The microwave filter of claim 10 and further comprising:

a substrate;

an acoustic reflector; and

the first, second and third acoustic resonators and the first and second plurality of intervening layers being supported upon the substrate by the acoustic reflector.

An microwave acoustic device fabricated upon a wafer comprising:

a first microwave filter fabricated upon the wafer and having a pass-band frequency and the first microwave filter comprising:

a first piezoelectric acoustic, bulk wave, resonator having a conducting electrode;

a second piezoelectric acoustic, bulk wave, resonator, the second acoustic resonator being acoustically coupled to the first acoustic resonator; and

